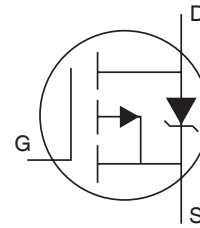


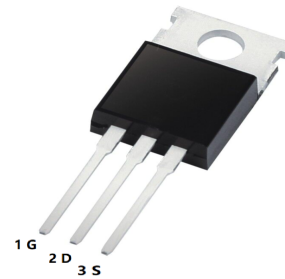
Description

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Features

- $V_{DS} (V) = -60V$
- $I_D = -31A (V_{GS} = -10V)$
- $R_{DS(ON)} < 60m\Omega (V_{GS} = -10V)$
- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated Lead-Free



Absolute Maximum Ratings

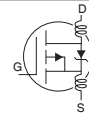
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-31	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-22	
I_{DM}	Pulsed Drain Current ①	-110	
$P_D @ T_C = 25^\circ C$	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	280	mJ
I_{AR}	Avalanche Current①	-16	A
E_{AR}	Repetitive Avalanche Energy①	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		1.4	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50		
$R_{\theta JA}$	Junction-to-Ambient		62	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-60			V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient		-0.034		V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance			60	mΩ	V _{GS} = -10V, I _D = -16A ④
V _{GS(th)}	Gate Threshold Voltage	-1.1	-2	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	8.0			S	V _{DS} = -25V, I _D = -16A
I _{DSS}	Drain-to-Source Leakage Current			-25 -250	μA	V _{DS} = -55V, V _{GS} = 0V V _{DS} = -44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage			100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage			-100	nA	V _{GS} = -20V
Q _g	Total Gate Charge			63	nC	I _D = -16A
Q _{gs}	Gate-to-Source Charge			13	nC	V _{DS} = -44V
Q _{gd}	Gate-to-Drain ("Miller") Charge			29	nC	V _{GS} = -10V, See Fig. 6 and 13 ④
t _{d(on)}	Turn-On Delay Time		14		ns	V _{DD} = -28V I _D = -16A R _G = 6.8Ω R _D = 1.6Ω, See Fig. 10 ④
t _r	Rise Time		66			
t _{d(off)}	Turn-Off Delay Time		39			
t _f	Fall Time		63			
L _D	Internal Drain Inductance		4.5		nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance		7.5			
C _{iss}	Input Capacitance		1200			V _{GS} = 0V pF V _{DS} = -25V f = 1.0MHz, See Fig. 5
C _{oss}	Output Capacitance		520			
C _{rss}	Reverse Transfer Capacitance		250			



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)			-31	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①			-110		
V _{SD}	Diode Forward Voltage			-1.3	V	T _J = 25°C, I _S = -16A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time		71	110	ns	T _J = 25°C, I _F = -16A
Q _{rr}	Reverse Recovery Charge		170	250	nC	di/dt = -100A/μs ④

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V_{DD} = -25V, starting T_J = 25°C, L = 2.1mH
R_G = 25Ω, I_{AS} = -16A. (See Figure 12)
- ③ I_{SD} ≤ -16A, di/dt ≤ -280A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

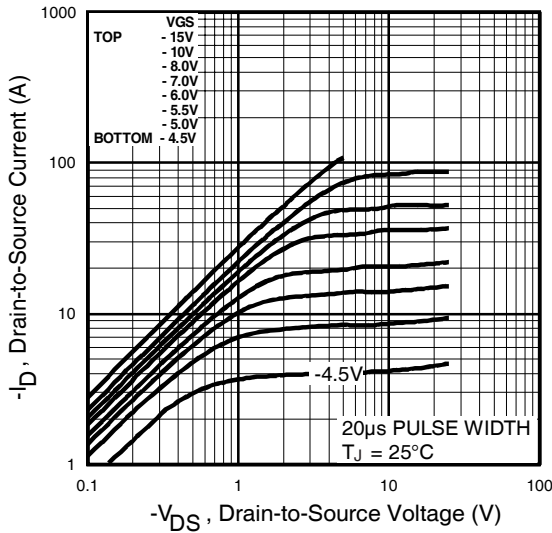


Fig 1. Typical Output Characteristics

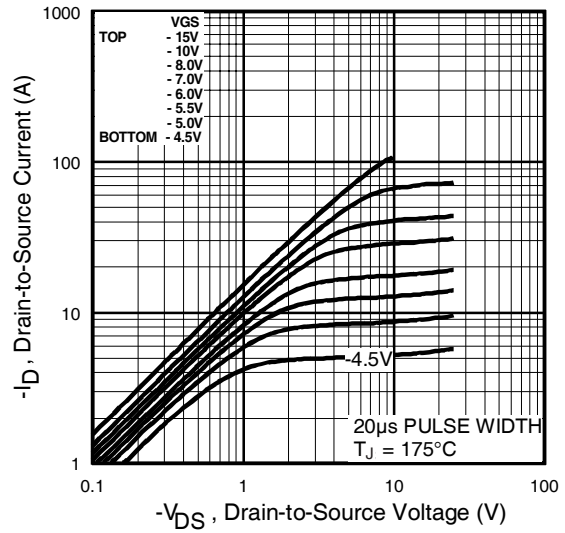


Fig 2. Typical Output Characteristics

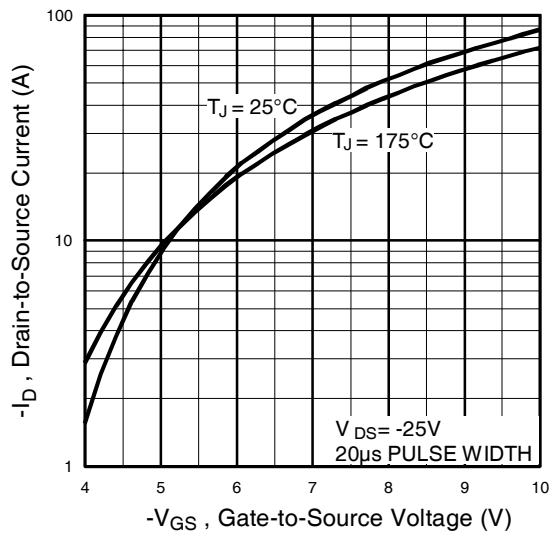


Fig 3. Typical Transfer Characteristics

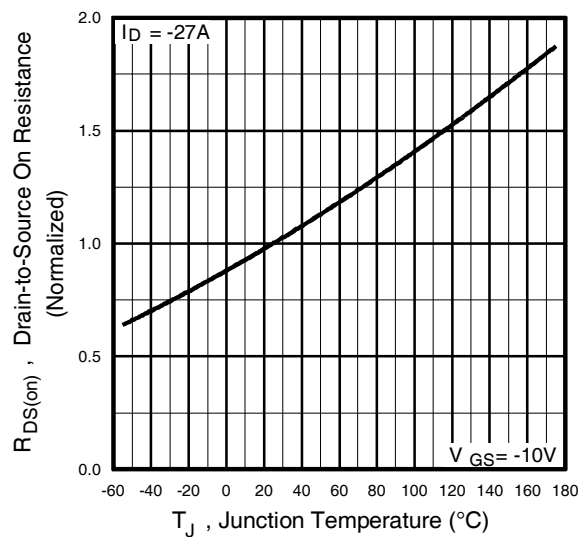


Fig 4. Normalized On-Resistance Vs. Temperature

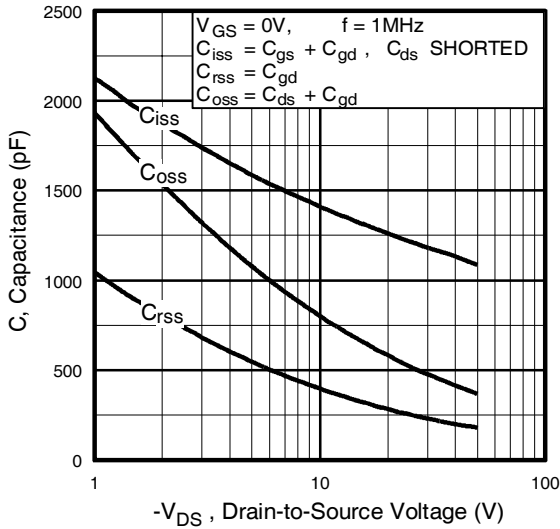


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

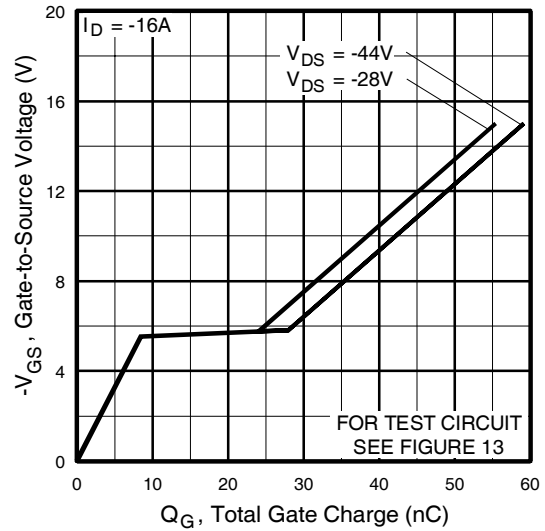


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

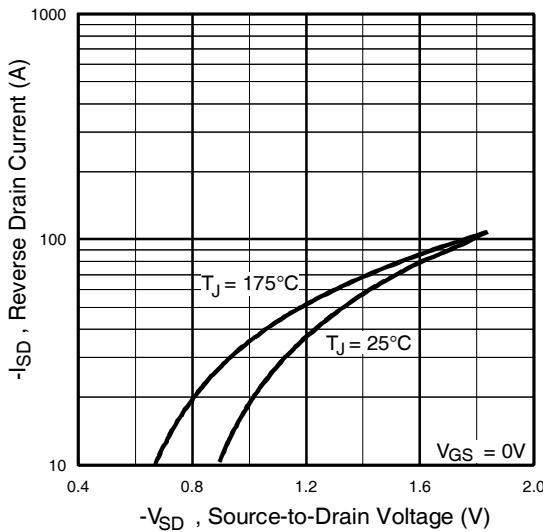


Fig 7. Typical Source-Drain Diode Forward Voltage

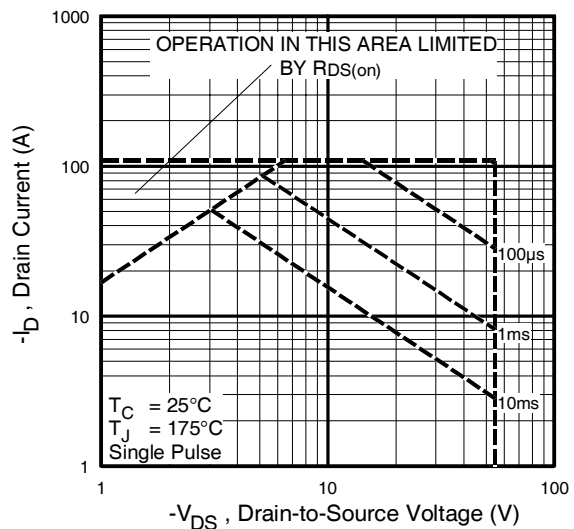


Fig 8. Maximum Safe Operating Area

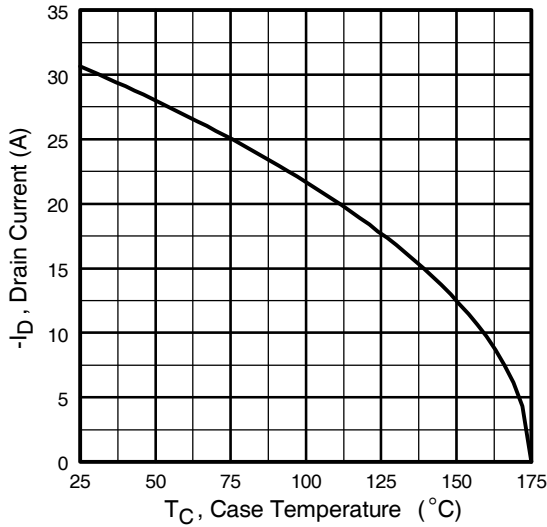


Fig 9. Maximum Drain Current Vs. Case Temperature

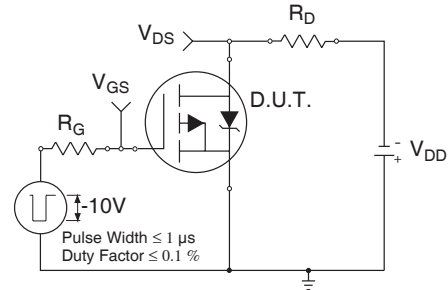


Fig 10a. Switching Time Test Circuit

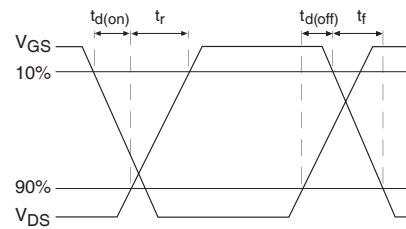


Fig 10b. Switching Time Waveforms

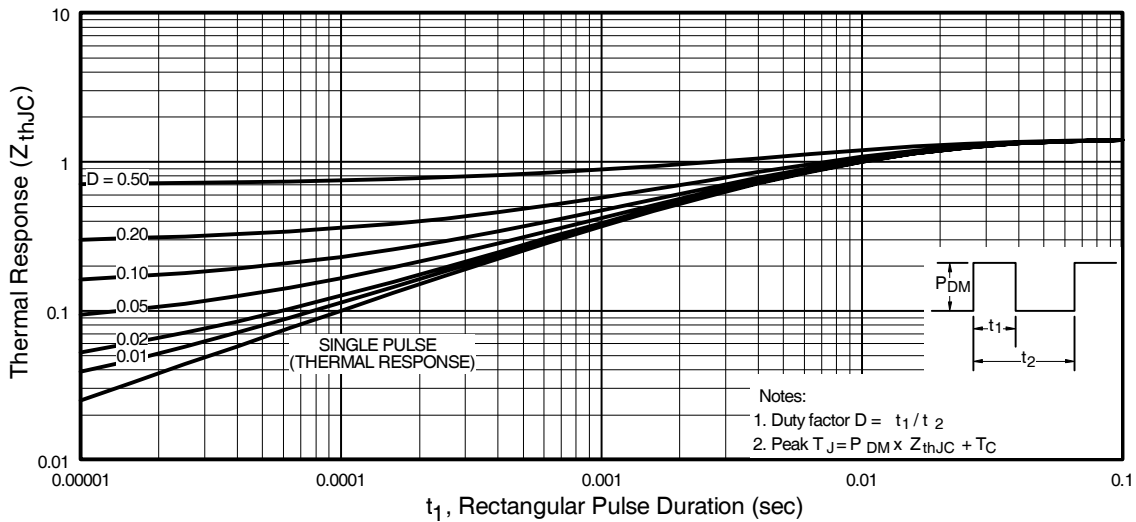


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

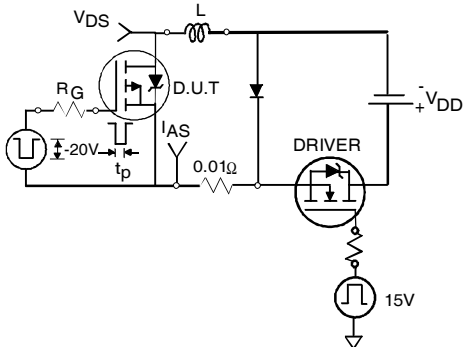


Fig 12a. Unclamped Inductive Test Circuit

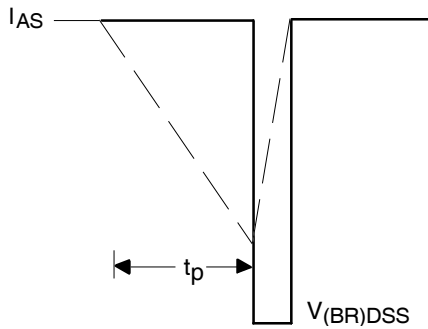


Fig 12b. Unclamped Inductive Waveforms

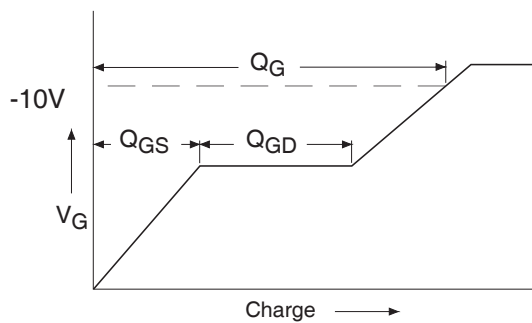


Fig 13a. Basic Gate Charge Waveform

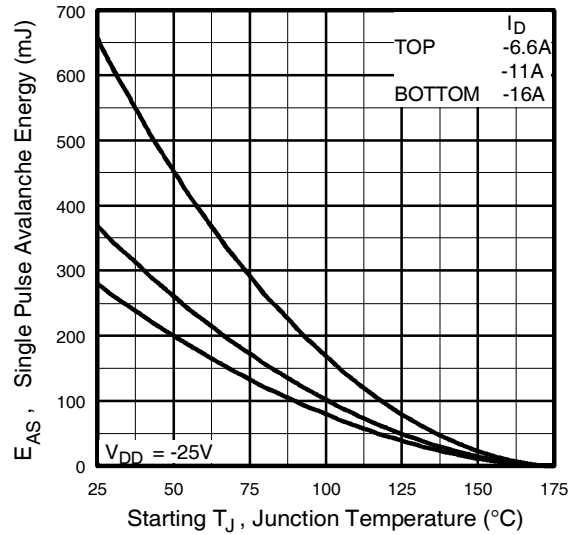


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

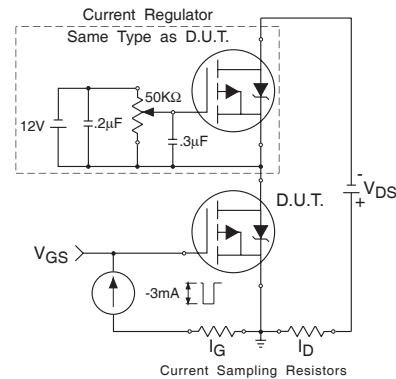
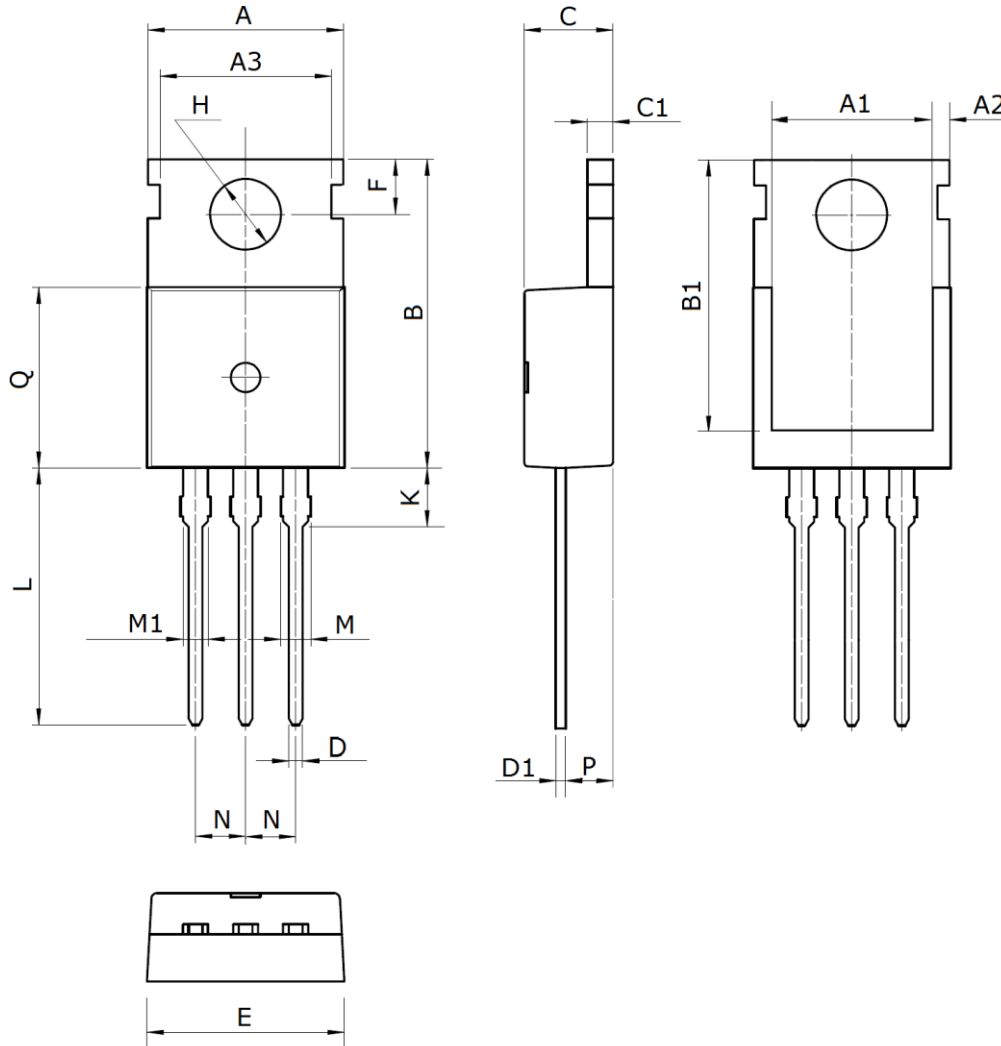


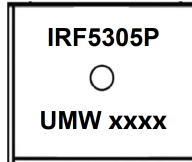
Fig 13b. Gate Charge Test Circuit

Package Mechanical Data TO-220



Symbol	Dimensions (mm)	Symbol	Dimensions (mm)	Symbol	Dimensions (mm)
A	10.0±0.3	C1	1.3±0.2	L	13.2±0.4
A1	8.0±0.2	D	0.8±0.2	M	1.38±0.1
A2	0.94±0.1	D1	0.5±0.1	M1	1.28±0.1
A3	8.7±0.1	E	10.0±0.3	N	2.54(typ)
B	15.6±0.4	F	2.8 ±0.1	P	2.4±0.3
B1	13.2±0.2	H	3.6±0.1	Q	9.15±0.25
C	4.5±0.2	K	3.1±0.2		

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW IRF5305PBF	TO-220	1000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)